

Title (en)
REMOVAL OF HIGH-DOSE ION-IMPLANTED PHOTORESIST USING SELF-ASSEMBLED MONOLAYERS IN SOLVENT SYSTEMS

Title (de)
ENTFERNEN VON HOCHIONENDOTIERTEM PHOTOLACK MIT SELBSTORGANISIERTEN MONOSCHICHTEN IN
LÖSUNGSMITTELSYSTEMEN

Title (fr)
ELIMINATION DE PHOTORESINE A IMPLANTATION IONIQUE HAUTE DOSE AU MOYEN DE MONOCOUCHEES AUTO-ASSEMBLEES DANS
DES SYSTEMES DE SOLVANTS

Publication
EP 1877530 A4 20100609 (EN)

Application
EP 06749725 A 20060410

Priority
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• US 67185105 P 20050415

Abstract (en)
[origin: WO2006113222A2] A method and self assembled monolayer (SAM)-containing compositions for removing bulk and hardened photoresist material from microelectronic devices have been developed. The SAM-containing composition includes at least one solvent, at least one catalyst, at least one SAM component, and optionally a surfactant. The SAM-containing compositions effectively remove the hardened photoresist material while simultaneously passivating the underlying silicon-containing layer(s) in a one step process.

IPC 8 full level
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CPC (source: EP KR)
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Citation (search report)
• [XYI] WO 03077032 A1 20030918 - SUPERCRITICAL SYSTEMS INC [US]
• [Y] US 6500605 B1 20021231 - MULLEE WILLIAM H [US], et al
• [E] WO 2006138505 A1 20061228 - ADVANCED TECH MATERIALS [US], et al

Designated contracting state (EPC)
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DOCDB simple family (publication)
WO 2006113222 A2 20061026; WO 2006113222 A3 20071108; CN 101198683 A 20080611; CN 101198683 B 20110914;
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TW 200700916 A 20070101

DOCDB simple family (application)
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